

LIQUID-CRYSTAL DISPLAY DRIVING CIRCUIT AND METHOD

BACKGROUND OF THE INVENTION

The present invention relates to a circuit and method for driving a liquid-crystal display, such as an active-matrix display employing thin-film transistors.

Active-matrix liquid-crystal displays or LCDs are widely employed in, for example, portable computers, where they provide the advantages of high-speed response and reduced crosstalk. In a typical active-matrix LCD, for each of the three primary colors, each picture element or pixel has a thin-film transistor (TFT) that is switched on and off by a signal received from a gate line, and a liquid-crystal capacitor that charges or discharges through a source line when the TFT is switched on. The source and gate lines form a matrix in which the gate lines are activated one at a time, and the source lines carry signals representing the displayed intensities of the picture elements. In the alternate-current or AC driving system that is usually employed with active-matrix LCDs, adjacent liquid-crystal capacitors are charged in opposite directions centered around a common potential. A more detailed description of the active-matrix circuit configuration and AC driving scheme will be given later.

In the AC driving scheme, as successive gate lines are activated, the voltage of each source line must swing alternately above and below the common potential. The voltage swings on the source lines are thereby doubled, as compared with direct-current driving. A resulting problem is that the time needed to charge the parasitic capacitances of the source lines is increased, current consumption is similarly increased, and large source-line driving circuits are needed. The large charging and discharging currents furthermore generate electrical noise.

Although the gate lines are not driven in an AC manner, they also have parasitic capacitances that must be charged and discharged. The charging and discharging of the gate lines similarly takes time, consumes current, generates noise, and requires large driving circuits.

SUMMARY OF THE INVENTION

It is accordingly an object of the present invention to reduce the current consumed in charging the parasitic capacitances of signal lines in a liquid-crystal display.

Another object of the invention is to reduce the time needed for charging the parasitic capacitances of signal lines in a liquid-crystal display.

Yet another object is to reduce electrical noise in a liquid-crystal display.

Still another object is to reduce the size and cost of the driving circuits of a liquid-crystal display.

The invented driving circuit drives a liquid-crystal display having first signal lines running in one direction, second signal lines running in another direction, switching elements controlled by the first signal lines, disposed at the intersections of the first and second signal lines, and liquid-crystal capacitors disposed at these same intersections and coupled through the switching elements to the second signal lines.

The driving circuit comprises a plurality of first drivers for sequentially driving the first signal lines to active and inactive levels, thereby switching the switching elements on and off, and a plurality of second drivers that drive the second signal lines with signals representing picture-element intensities.

According to a first aspect of the invention, a switching circuit is coupled to the second signal lines. At transition times when any of the first signal lines change

between the active and inactive levels, the switching circuit disconnects the second signal lines from the second drivers, and places the second signal lines in a short-circuited state. The second signal lines may be short-circuited to a fixed potential, or short-circuited to each other.

According to a second aspect of the invention, a switching circuit is coupled to the first signal lines. When a pair of first signal lines changes between the active and inactive levels, the switching circuit disconnects that pair of first signal lines from the corresponding first drivers, and places that pair of first signal lines in a short-circuited state. The short-circuited pair of first signal lines may be short-circuited to a fixed potential, or short-circuited to each other.

The switching circuits in both the first and second aspects of the invention may incorporate resistors to limit the peak current flow on the short-circuited signal lines.

According to a third aspect of the invention, the second drivers drive each of the second signal lines alternately above and below a certain center potential. Each second signal line stays at potentials equal to or greater than the center potential while a plurality of first signal lines are being driven to the active level, then stays at potentials equal to or less than the center potential while another plurality of first signal lines are being driven to the active level.

The first and second aspects of the invention recycle charge from one signal line to another through the short circuits, thereby reducing current consumption, reducing electrical noise, and enabling the signal lines to be driven more rapidly, or to be driven by drivers with less driving capability, hence with smaller size and lower cost.

The third aspect of the invention provides similar

effects by reducing the frequency with which the second signal lines are driven from one side of the center potential to the opposite side.

BRIEF DESCRIPTION OF THE DRAWINGS

In the attached drawings:

FIG. 1 is a circuit diagram of a conventional active-matrix LCD;

FIG. 2 is a timing diagram illustrating a conventional gate-line driving scheme;

FIG. 3 is a timing diagram illustrating a conventional source-line driving scheme;

FIG. 4 is a circuit diagram of an active-matrix LCD embodying the present invention;

FIG. 5 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 6 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 7 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 8 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 9 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 10 is a timing diagram of a source-line driving scheme according to the present invention;

FIG. 11 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 12 is a waveform diagram illustrating the driving of the gate lines in FIG. 11;

FIG. 13 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 14 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 15 is a circuit diagram of another active-matrix LCD embodying the present invention;

FIG. 16 is a circuit diagram of another active-matrix LCD embodying the present invention; and

FIG. 17 is a circuit diagram of another active-matrix LCD embodying the present invention.

DETAILED DESCRIPTION OF THE INVENTION

Embodiments of the invention will be described with reference to the attached illustrative drawings, following a description of the circuit elements that are common to these embodiments and the conventional art, and a description of the AC driving scheme employed in the conventional art.

Referring to FIG. 1, a conventional active-matrix LCD comprises an LCD panel 1, a gate-line driving circuit 2, and a source-line driving circuit 3. The LCD panel 1 comprises a liquid crystal encapsulated between a pair of flat transparent plates. A matrix of gate lines G_1 to G_n , running horizontally in the drawing, and source lines S_1 to S_m , running vertically in the drawing, is formed on one of the transparent plates. Thin-film transistors TR_{11} to TR_{nm} are formed at the intersections of the gate lines and source lines. Each thin-film transistor TR_{ij} has a gate terminal coupled to the corresponding gate line G_i , a source terminal coupled to the corresponding source line S_j , and a drain terminal coupled to one electrode of a corresponding liquid-crystal capacitor CX_{ij} (where i is an integer from one to n , and j is an integer from one to m). As their other electrodes, the liquid-crystal capacitors CX_{11} to CX_{nm} share a common electrode formed on the opposing transparent plate. The common electrode is held at a fixed potential V_{com} . (The transparent plates, liquid crystal, and common electrode are not explicitly shown in the drawing.)

As the source lines S_1 to S_m also face the common

electrode, substantial parasitic capacitances CS_1 to CS_m exist between the source lines and the common electrode. Similarly, parasitic capacitances CG_1 to CG_n exist between the gate lines G_1 to G_n and the common electrode.

The gate-line driving circuit 2 comprises gate drivers GD_1 to GD_n that drive the corresponding gate lines G_1 to G_n to an active potential, referred to below as the high level, to switch on the connected thin-film transistors, and to an inactive potential, referred to below as the low level, to switch the thin-film transistors off.

The source-line driving circuit 3 comprises source drivers SD_1 to SD_m that drive the corresponding source lines S_1 to S_m to potentials equal to, greater than, or less than a certain center potential. The center potential is equal to, or nearly equal to, V_{com} . The output potentials of the source drivers can be varied in, for example, sixty-four steps on each side of the center potential, enabling sixty-four intensity levels to be displayed.

The circuit elements shown in FIG. 1 are also present in the embodiments of the invention that will be described later, and will be denoted by the same reference characters, without repeated descriptions. The parasitic capacitances CS_1 to CS_m and CG_1 to CG_n are also present, even when not shown in the drawings.

FIG. 2 illustrates the conventional gate-line driving scheme, the horizontal axis representing time. To display one frame of an image, the gate lines are driven to the high level in turn, in sequence from G_1 to G_n , only one gate line being driven high at a time. The same driving sequence is then repeated to display the next frame.

FIG. 3 illustrates the conventional AC driving of two adjacent source lines S_{k-1} and S_k , the horizontal axis representing time on the same scale as in FIG. 2. During the interval while the first gate line G_1 is high, each pair

of mutually adjacent source lines is driven to potentials on opposite sides of the center potential, shown in the drawing as V_{com} . For example, source line S_{k-1} is driven to a potential equal to or greater than V_{com} , while source line S_k is driven to a potential equal to or less than V_{com} . The dotted lines within the waveforms indicate that there are a plurality of possible potential levels above and below V_{com} .

During the next interval, while gate line G_2 is being driven high, source lines such as S_{k-1} that previously carried potentials equal to or greater than V_{com} are now driven to potentials equal to or less than V_{com} . Similarly, source lines such as S_k that previously carried potentials equal to or less than V_{com} are now driven to potentials equal to or greater than V_{com} .

In the next interval, while gate line G_3 is high, the potentials of the source lines are again reversed with respect to the center potential V_{com} . The source line potentials continue to reverse around V_{com} as each successive gate line is driven, until the end of the frame.

The parasitic capacitance of each source line is approximately one hundred fifty picofarads (150 pF), while the capacitance of one of the liquid-crystal capacitors, e.g. CX_{11} , is only about eight picofarads (8 pF). Most of the current generated by the source line drivers is therefore consumed in charging or discharging the parasitic capacitance of the source lines, rather than in charging or discharging the liquid-crystal capacitors.

FIG. 4 shows a first embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements shown in FIG. 1.

The source-line driving circuit 10 in the first embodiment has a switching circuit 11 comprising switches SWA_1 to SWA_m and SWB_1 to SWB_m . Switch SWA_j couples source line S_j to source driver SD_j ($j = 1, \dots, m$), while switch

SWB_j couples source line S_j to a common electrode (not visible) held at the potential V_{com} of the common electrode of the liquid-crystal capacitors. Switches SWA_j and SWB_j comprise, for example, field-effect transistors. This type of switching circuit 11 can easily be added to existing source-line driving circuit designs.

The switches SWA_j and SWB_j are controlled in synchronization with the gate drivers GD_1 to GD_n . Normally, switches SWA_j are all closed, and switches SWB_j are all open. At times of transition of the gate lines G_1 to G_n between the high and low levels, however, for a brief interval switches SWA_j are opened, and switches SWB_j are closed, thereby disconnecting the source lines from the source drivers and short-circuiting the source lines to V_{com} .

Referring again to FIGs. 2 and 3, during most of the interval when gate line G_1 is high, switches SWA_j are closed and switches SWB_j are open, enabling the source drivers SD_j to charge the liquid-crystal capacitors CX_{1j} to signal levels representing the first row of picture-element intensities. As in the conventional art, half of the source lines, including source line S_{k-1} , are driven to potentials equal to or greater than a center potential approximately equal to V_{com} , while the other half of the source lines, including source line S_k , are driven to potentials equal to or less than the same center potential.

At the instant when gate driver GD_1 drives gate line G_1 from the high level to the low level, and gate driver GD_2 drives gate line G_2 from the low level to the high level, switches SWA_j are all opened, and switches SWB_j are all closed, shorting all of the source lines to V_{com} . Charge is thereby circulated from the source lines (e.g. S_{k-1}) at potentials above V_{com} to the source lines (e.g. S_k) at potentials below V_{com} , speedily bringing all of the source

lines to the V_{com} potential, with little or no net current flow into or out of the source-line driving circuit 10.

After a brief interval, when this recycling of charge has been substantially completed, and when gate line G_2 has reached the high level and gate line G_1 has reached the low level, switches SWB_j are opened and switches SWA_j are closed, coupling the source lines S_j to their source drivers SD_j . The source drivers then drive the source lines and liquid-crystal capacitors CX_{2j} to signal levels representing the next row of picture-element intensities.

By recycling charge among the source lines, the first embodiment reduces the current consumption of the source-line driving circuit 10 to substantially half the value in the conventional art. Electrical noise on the power-supply and ground lines of the source drivers is correspondingly reduced. The frame rate can also be increased, because substantially half of the work of charging and discharging the source lines is done by the switching circuit 11, which has a lower internal impedance than the output impedance of the source drivers, and therefore permits faster charging and discharging.

Alternatively, for a given frame rate, the driving capability and hence the size of the source drivers can be reduced.

The first embodiment is not restricted to the AC driving scheme illustrated in FIGs. 2 and 3. The first embodiment provides the same effects in any driving scheme that simultaneously drives half of the source lines to potentials above a center potential substantially equal to V_{com} , and approximately half of the source lines to potentials below the center potential, and sometimes reverses the potentials of the source lines with respect to the center potential. The switching circuit operates to short-circuit the source lines to V_{com} whenever the

potentials of the source lines are about to be reversed with respect to the center potential.

FIG. 5 shows a second embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements in FIG. 1.

The source-line driving circuit 12 in the second embodiment has a switching circuit 13 comprising switches SWC_1 to SWC_m and SWD_1 to SWD_{m-1} . Switch SWC_j couples source line S_j to source driver SD_j ($j = 1, \dots, m$), while switch SWD_j couples source line S_j to source line S_{j+1} ($j = 1, \dots, m - 1$). Switches SWC_j and SWD_j comprise, for example, field-effect transistors, and can easily be added to existing source-line driving circuit designs.

The control of switches SWC_j and SWD_j is analogous to the control of switches SWA_j and SWB_j in the first embodiment. Normally, switches SWC_j are all closed, and switches SWD_j are all open. At each transition of any of the gate lines G_1 to G_n between the high and low levels, for a brief interval switches SWC_j are opened, and switches SWD_j are closed, thereby disconnecting the source lines from the source drivers and mutually short-circuiting all adjacent pairs of source lines.

The second embodiment operates in the same way as the first embodiment, except that when switches SWD_j are closed, charge is circulated directly among the source lines, instead of being circulated through a common electrode held at the V_{com} potential. The resulting potential of the short-circuited source lines is the average potential to which the source lines were driven during the preceding gate-line driving interval. This average potential will usually be close to V_{com} .

The second embodiment provides substantially the same effects as the first embodiment, without the need for a separate electrode, held at the V_{com} potential, to which the

source lines can be short-circuited.

FIG. 6 shows a third embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements in FIG. 1.

The source-line driving circuit 14 in the third embodiment has a switching circuit 15 comprising switches $SWC_1, SWC_2, \dots, SWC_m$ and $SWD_1, SWD_3, \dots, SWD_{m-1}$. Switching circuit 15 is obtained from the switching circuit 13 of the second embodiment by removing the even-numbered switches $SWD_2, SWD_4, \dots, SWD_{m-2}$ that short-circuit adjacent source lines.

The third embodiment operates in the same way as the second embodiment, but when switches SWC_j ($j = 1, 2, \dots, m$) are opened and switches SWD_j ($j = 1, 3, \dots, m - 1$) are closed, each source line is short-circuited to just one adjacent source line. Since adjacent source lines are driven to potentials on opposite sides of a center potential approximately equal to V_{com} , each short-circuited pair of source lines is brought to a potential in the general vicinity of V_{com} .

The third embodiment accordingly provides generally the same effects as the second embodiment, while requiring fewer switches.

FIG. 7 shows a fourth embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements in FIG. 1.

The source-line driving circuit 16 in the fourth embodiment has a switching circuit 17 with the same switches SWA_1 to SWA_m and SWB_1 to SWB_m as in the first embodiment, but adds a resistor R_1 between each of switches SWB_1 to SWB_m and the V_{com} electrode. These resistors R_1 comprise, for example, field-effect transistors configured to provide a certain resistance; such resistors can easily be fabricated within the switching circuit 17. The resistors R_1 limit the

peak current flow on the source lines S_1 to S_m when switches SWB_1 to SWB_m are closed.

In the first embodiment, when the source lines are short-circuited directly to V_{com} , if the source lines discharge to V_{com} too rapidly, capacitive coupling between the source lines and gate lines may generate voltage noise on the gate lines in the LCD panel 1, possibly causing thin-film transistors TR_{ij} to switch on at unwanted times. Transistors that are disposed far from the gate drivers GD_i are particularly susceptible to such noise.

In the fourth embodiment, the resistors R_1 in the switching circuit 17 reduce the voltage noise on the gate lines by limiting the rate of discharge of the source lines. The resistance of the resistors R_1 should be high enough to prevent voltage noise problems, without being so high as to slow the flow of charge unduly. The fourth embodiment then provides substantially the same effects as the first embodiment, without possible unwanted switching of the thin-film transistors during the intervals when the source lines are short-circuited to V_{com} .

FIG. 8 shows a fifth embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements in FIG. 1.

The source-line driving circuit 18 in the fifth embodiment has a switching circuit 19 with the same switches SWC_1 to SWC_m and SWD_1 to SWD_{m-1} as in the second embodiment, but adds a resistor R_2 between each switch SWD_j and source line S_{j+1} ($j = 1, \dots, m - 1$). As in the fourth embodiment, these resistors R_2 can be fabricated as field-effect transistors configured to provide a certain resistance, limiting the peak current flow on the source lines S_1 to S_m when switches SWD_1 to SWD_{m-1} are closed.

The operation of the fifth embodiment can be understood from the description of the second and fourth embodiments.

The fifth embodiment provides substantially the same effects as the second embodiment, while reducing voltage noise in the LCD panel 1 during the intervals while the source lines are mutually short-circuited.

As a variation of the fifth embodiment, the even-numbered switches SWD_2 , SWD_4 , ... and their corresponding resistors R_2 can be eliminated, as in the third embodiment.

FIG. 9 shows a sixth embodiment of the invention. The LCD panel 1 and gate-line driving circuit 2 are similar to the conventional elements in FIG. 1.

The source-line driving circuit 20 in the sixth embodiment has a switching circuit 21 with the same switches SWA_1 to SWA_m and SWB_1 to SWB_m as in the first embodiment, but switches SWB_1 to SWB_m couple the source lines to a common electrode held at a voltage $V_{SD/2}$ slightly different from the common potential V_{com} applied to the liquid-crystal capacitors. $V_{SD/2}$ is the center potential of the driving range of the source drivers.

The driving range of the source drivers is not centered exactly around V_{com} for the following reason. When a gate line is driven from the high level to the low level to switch off the connected thin-film transistors, the potential change on the gate line causes a slight shift ΔV_{GD} in the drain potential of the thin-film transistors in the LCD panel 1, due to capacitive coupling C_{GD} between the gates and drains of the thin-film transistors. The drain potential of a thin-film transistor is also the potential of the connected electrode of a liquid-crystal capacitor, so the potentials stored in the liquid-crystal capacitors are shifted by ΔV_{GD} from the potentials to which the source lines were driven.

If the source lines are driven alternately above and below V_{com} , the ΔV_{GD} potential shift creates slight unwanted shifts in displayed intensity levels, and produces

a slight display flicker. The source drivers in the sixth embodiment are therefore configured to drive the source lines to potentials alternately above and below a center potential $V_{SD/2}$ offset by ΔV_{GD} from the common potential V_{com} . Since the source-line driving circuit 20 provides $V_{SD/2}$ as a reference potential to the source drivers, it is a simple matter to supply $V_{SD/2}$ to the switches SWB_1 to SWB_m as well.

The sixth embodiment operates in the same way as the first embodiment, but since the source lines are short-circuited to the true center potential $V_{SD/2}$ instead of V_{com} , the average total current flow between the source lines and the common $V_{SD/2}$ electrode has no direct-current component. Current consumption is therefore reduced even more than in the first embodiment.

A similar modification can be made to the fourth embodiment by coupling the resistors R_1 to a common electrode held at $V_{SD/2}$ instead of V_{com} .

As a seventh embodiment of the invention, FIG. 10 illustrates a method of driving the source lines in which source line S_{k-1} is driven to potentials equal to or greater than V_{com} while the first three gate lines G_1 , G_2 , and G_3 are driven high, then to potentials equal to or less than V_{com} while the next three gate lines G_4 , G_5 , and G_6 are driven high, and so on in a similar manner, the driving potential being reversed with respect to V_{com} only one-third as often as in the conventional art. Mutually adjacent source lines, such as S_{k-1} and S_k , are still driven in opposite directions from V_{com} , as shown.

This driving method can be practiced with the conventional driving circuit shown in FIG. 1. Since adjacent picture elements tend to have similar intensities, as successive gate lines are activated, the signal levels on the source lines tend not to change very much, except at

times of reversal with respect to V_{com} . In the seventh embodiment, current consumption at the times when gate lines G_2, G_3, G_5, \dots are being driven high is greatly reduced. The source-line driving circuit consumes a large amount of current only when every third gate line (G_1, G_4, \dots) is driven high.

This driving method can also be combined with any of the preceding embodiments of the invention, short-circuiting the source lines only when every third gate line (G_1, G_4, \dots) is driven high. $V_{SD/2}$ may be substituted for V_{com} , as in the sixth embodiment.

The driving method of the seventh embodiment can be generalized by reversing the driving potential with respect to V_{com} (or $V_{SD/2}$) once every N gate lines, where N is any integer equal to or greater than two.

The preceding embodiments have been concerned with the source-line driving circuit. The following embodiments are concerned with the gate-line driving circuit.

FIG. 11 shows an eighth embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 22 in the eighth embodiment has a switching circuit 23 comprising switches SWE_1 to SWE_n and SWF_1 to SWF_n . Switch SWE_i couples gate line G_i to gate driver GD_i ($i = 1, \dots, n$). Switch SWF_i couples gate line G_i to a common electrode (not visible) held at a potential $V_{GD/2}$ halfway between the high and low levels to which the gate lines are driven. Switches SWE_i and SWF_i comprise, for example, field-effect transistors, and can easily be added to existing gate-line driving circuit designs.

The switches SWE_i and SWF_i are controlled in synchronization with the gate drivers as follows. Normally, switches SWE_i are all closed, and switches SWF_i are all

open. When the gate drivers GD_{i-1} and GD_i drive gate line G_{i-1} from the high level to the low level and gate line G_i from the low level to the high level, for a brief transition interval switches SWE_{i-1} and SWE_i are opened, and switches SWF_{i-1} and SWF_i are closed, thereby disconnecting the pair of gate lines G_{i-1} and G_i from gate drivers GD_{i-1} and GD_i , and short-circuiting this pair of gate lines to the $V_{GD/2}$ electrode.

The operation of the eighth embodiment will be described with reference to the waveform diagram in FIG. 12.

During the interval marked T, the first gate driver GD_1 generates the high level and the other gate drivers generate the low level.

During a transition time Δt , the first gate driver GD_1 changes from high to low output, and the second gate driver GD_2 changes from low to high output. Switches SWE_1 and SWE_2 are opened during this transition time Δt , disconnecting gate lines G_1 and G_2 from gate drivers GD_1 and GD_2 . Switches SWF_1 and SWF_2 are closed during the transition time Δt , so the first gate line G_1 quickly discharges from the high level to the intermediate level $V_{GD/2}$, and the second gate line quickly charges from the low level to the same intermediate level $V_{GD/2}$. Charge is thereby recycled from the first gate line G_1 through the $V_{GD/2}$ electrode to the second gate line G_2 .

At the end of the transition interval Δt , switches SWF_1 and SWF_2 are opened and switches SWE_1 and SWE_2 are closed, connecting gate drivers GD_1 and GD_2 to gate lines G_1 and G_2 again. Gate drivers GD_1 and GD_2 now complete the process of driving gate line G_1 low and gate line G_2 high.

A similar procedure is followed when the other gate lines are driven high and low. As a result, substantially half of the charge stored in the parasitic capacitance of each gate line is circulated to the next gate line, and the

gate line drivers have to supply only half as much current as in the conventional art. Current consumption and electrical noise are thereby reduced.

The gate line drivers in the eighth embodiment require less driving capability than in the conventional art, and can be made correspondingly smaller. The size and cost of the gate-line driving circuit 22 can accordingly be reduced. These effects are obtained regardless of the driving method employed for the source lines.

FIG. 13 shows a ninth embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 24 in the ninth embodiment has a switching circuit 25 similar to the switching circuit 23 in the eighth embodiment, with switches SWE_1 to SWE_n and SWF_1 to SWF_n , but supplies switches SWF_1 to SWF_n with the common potential V_{com} instead of $V_{GD}/2$.

Aside from this difference, the ninth embodiment operates in the same way as the eighth embodiment, so a detailed description will be omitted. If V_{com} is intermediate between the high and low levels output by the gate drivers, as is normally the case, then when each gate line is driven from the high level to the low level, some of the charge stored in the parasitic capacitance of each gate line is circulated to the next gate line, permitting the driving capacity of the gate drivers, and the size and cost of the gate-line driving circuit 24, to be reduced accordingly.

Compared with the eighth embodiment, the ninth embodiment has the advantage of not requiring extra circuitry for generating the $V_{GD}/2$ potential.

FIG. 14 shows a tenth embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 26 in the tenth embodiment has a switching circuit 27 comprising switches SWG_1 to SWG_n and SWH_1 to SWH_{n-1} . Switch SWG_j couples gate line G_j to gate driver GD_j ($j = 1, \dots, n$). Switch SWH_j couples gate line G_j to gate line G_{j+1} ($j = 1, \dots, n - 1$). Switches SWG_j and SWH_j comprise, for example, field-effect transistors, and can easily be added to existing gate-line driving circuit designs.

The switches SWG_j and SWH_j are controlled as follows. Normally, switches SWG_j are all closed, and switches SWH_j are all open. At each transition of any pair of gate lines G_{i-1} to G_i between the high and low levels, for a brief interval Δt , switches SWG_{i-1} and SWG_i are opened and switch SWH_{i-1} is closed, thereby disconnecting gate lines G_{i-1} and G_i from gate drivers GD_{i-1} and GD_i and mutually short-circuiting gate lines G_{i-1} and G_i to each other.

The tenth embodiment provides substantially the same effect as the eighth embodiment, by recycling substantially half the charge stored in the parasitic capacitance of gate line G_{i-1} directly to gate line G_i . The necessary driving capacity of the gate drivers is thereby reduced, and the size and cost of the gate-line driving circuit 26 can be reduced. The tenth embodiment also has the advantage of not requiring extra circuitry for generating the $V_{GD/2}$ potential, or for supplying the common potential V_{com} to the gate-line driving circuit 26.

FIG. 15 shows an eleventh embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 28 in the eleventh embodiment has a switching circuit 29 with the same switches SWE_1 to SWE_n and SWF_1 to SWF_n as in the eighth embodiment, but adds a resistor R_3 between each of switches SWF_1 to SWF_n and the $V_{GD/2}$ electrode. These resistors R_3 comprise, for

example, field-effect transistors configured to provide a certain resistance, limiting the peak current flow on the gate lines G_1 to G_n when switches SWF_1 to SWF_m are closed.

Resistors R_3 reduce voltage noise on the signal lines (not visible) that supply the intermediate potential $V_{GD}/2$ to the gate-line driving circuit 28. Voltage noise on the source lines S_1 and S_m due to capacitive coupling with the gate lines at the points where the source lines and gate lines intersect is also reduced.

FIG. 16 shows a twelfth embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 30 in the twelfth embodiment has a switching circuit 31 with the same switches SWE_1 to SWE_n and SWF_1 to SWF_n as in the ninth embodiment, but adds a resistor R_3 between each of switches SWF_1 to SWF_n and the V_{com} electrode. These resistors R_3 are similar to the resistors R_3 in the eleventh embodiment, limiting the peak current flow on the gate lines G_1 to G_n when switches SWF_1 to SWF_m are closed, thereby reducing voltage noise on the signal lines (not visible) that supply the common potential V_{com} to the gate-line driving circuit 30, and voltage noise on the source lines S_1 and S_m due to capacitive coupling with the gate lines.

FIG. 17 shows a thirteenth embodiment of the invention. The LCD panel 1 and source-line driving circuit 3 are similar to the conventional elements in FIG. 1.

The gate-line driving circuit 32 in the thirteenth embodiment has a switching circuit 33 with the same switches SWG_1 to SWG_n and SWH_1 to SWH_{n-1} as in the tenth embodiment, but adds a resistor R_4 between each switch SWH_i and gate line G_{i+1} ($i = 1, \dots, n - 1$). These resistors R_4 are similar to the resistors R_3 in the eleventh and twelfth embodiments, limiting the peak current flow on the gate

lines G_1 and G_{i+1} when switch SWH_i is closed, thereby reducing voltage noise on the source lines S_1 and S_m due to capacitive coupling with the gate lines.

The eleventh, twelfth, and thirteenth embodiments provide the same effects as the eight, ninth, and tenth embodiments, respectively, with the added effect of a reduction in electrical noise.

Any of the eighth to thirteenth embodiments can be combined with any of the first to seventh embodiments to reduce current consumption, electrical noise, size, and cost in both the source-line driving circuits and the gate-line driving circuits.

Applications of the present invention are not limited to portable computers. The invention can be practiced in driving circuits for various types of liquid-crystal displays, including LCD flat-panel television sets, and projection television sets with liquid-crystal light valves.

The switching elements in the LCD panel need not be thin-film transistors. The invented driving circuits can also be used to drive LCD panels employing thin-film diode switching elements, metal-insulator-metal (MIM) switching elements, and various other types of nonlinear switching elements. Depending on the types of switching elements employed, the signal lines in the matrix may have names other than source lines and gate lines.

The driving methods are not limited to the waveforms shown in the drawings. The gate driving signals may be active low instead of active high. The eighth to thirteenth embodiments can reduce the required driving capability of a driving circuit that drives the gate lines or equivalent lines in any type of LCD matrix, whether active or not.

Those skilled in the art will recognize that further variations are possible within the scope claimed below.